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## FAIRCHILD



## FGA25S125P

## 1250 V, 25 A Shorted-anode IGBT

## General Description

Using advanced field stop trench and shorted-anode technology, Fairchild's shorted-anode trench IGBTs offer superior conduction and switching performances for soft switching applications. The device can operate in parallel configuration with exceptional avalanche capability. This device is designed for induction heating and microwave oven.

## Applications

- Induction Heating, Microwave Oven


## Features

- High Speed Switching
- Low Saturation Voltage: $\mathrm{V}_{\mathrm{CE}(\mathrm{sat})}=1.8 \mathrm{~V} @ \mathrm{I}_{\mathrm{C}}=25 \mathrm{~A}$
- High Input Impedance
- RoHS Compliant


## Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
| :---: | :---: | :---: | :---: | :---: | :---: |
| FGA25S125P | FGA25S125P <br> _SN00337 | TO-3PN | - | - | 30 |

Electrical Characteristics of the IGBT $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Off Characteristics |  |  |  |  |  |  |
| BV ${ }_{\text {CES }}$ | Collector to Emitter Breakdown Voltage | $\mathrm{V}_{\mathrm{GE}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=1 \mathrm{~mA}$ | 1250 | - | - | V |
| $\frac{\Delta \mathrm{BV}_{\mathrm{CES}}}{\Delta \mathrm{~T}_{\mathrm{J}}}$ | Temperature Coefficient of Breakdown Voltage | $\mathrm{V}_{\mathrm{GE}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=1 \mathrm{~mA}$ | - | 1.2 | - | V/ ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{I}_{\text {ces }}$ | Collector Cut-Off Current | $\mathrm{V}_{\mathrm{CE}}=1250 \mathrm{~V}, \mathrm{~V}_{\mathrm{GE}}=0 \mathrm{~V}$ | - | - | 1 | mA |
| $\mathrm{I}_{\text {GES }}$ | G-E Leakage Current | $\mathrm{V}_{\mathrm{GE}}=\mathrm{V}_{\mathrm{GES}}, \mathrm{V}_{\mathrm{CE}}=0 \mathrm{~V}$ | - | - | $\pm 500$ | nA |
| On Characteristics |  |  |  |  |  |  |
| $\mathrm{V}_{\mathrm{GE} \text { (th) }}$ | G-E Threshold Voltage | $\mathrm{I}_{\mathrm{C}}=25 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=\mathrm{V}_{\mathrm{GE}}$ | 4.5 | 6.0 | 7.5 | V |
| $\mathrm{V}_{\mathrm{CE} \text { (sat) }}$ | Collector to Emitter Saturation Voltage | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=25 \mathrm{~A}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V} \\ & \mathrm{~T}_{\mathrm{C}}=25^{\circ} \mathrm{C} \end{aligned}$ | - | 1.8 | 2.35 | V |
|  |  | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=25 \mathrm{~A}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V} \\ & \mathrm{~T}_{\mathrm{C}}=125^{\circ} \mathrm{C} \\ & \hline \end{aligned}$ | - | 2.05 | - | V |
|  |  | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=25 \mathrm{~A}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V}, \\ & \mathrm{~T}_{\mathrm{C}}=175^{\circ} \mathrm{C} \end{aligned}$ | - | 2.16 | - | V |
| $V_{F M}$ | Diode Forward Voltage | $\mathrm{I}_{\mathrm{F}}=25 \mathrm{~A}, \mathrm{~T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ | - | 1.7 | 2.4 | V |
|  |  | $\mathrm{I}_{\mathrm{F}}=25 \mathrm{~A}, \mathrm{~T}_{\mathrm{C}}=175^{\circ} \mathrm{C}$ | - | 2.1 | - | V |
| Dynamic Characteristics |  |  |  |  |  |  |
| $\mathrm{C}_{\text {ies }}$ | Input Capacitance | $\begin{aligned} & V_{\mathrm{CE}}=30 \mathrm{~V}, \mathrm{~V}_{\mathrm{GE}}=0 \mathrm{~V}, \\ & \mathrm{f}=1 \mathrm{MHz} \end{aligned}$ | - | 2150 | - | pF |
| $\mathrm{C}_{\text {oes }}$ | Output Capacitance |  | - | 48 | - | pF |
| $\mathrm{C}_{\text {res }}$ | Reverse Transfer Capacitance |  | - | 36 | - | pF |
| Switching Characteristics |  |  |  |  |  |  |
| $\mathrm{t}_{\mathrm{d} \text { (on) }}$ | Turn-On Delay Time | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}}=600 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=25 \mathrm{~A}, \\ & \mathrm{R}_{\mathrm{G}}=10 \Omega, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V}, \\ & \text { Resistive Load, } \mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C} \end{aligned}$ | - | 24 | - | ns |
| $\mathrm{t}_{\mathrm{r}}$ | Rise Time |  | - | 250 | - | ns |
| $\mathrm{t}_{\text {d(off) }}$ | Turn-Off Delay Time |  | - | 502 | - | ns |
| $\mathrm{t}_{\mathrm{f}}$ | Fall Time |  | - | 138 | - | ns |
| $\mathrm{E}_{\text {on }}$ | Turn-On Switching Loss |  | - | 1085 | - | uJ |
| $\mathrm{E}_{\text {off }}$ | Turn-Off Switching Loss |  | - | 580 | - | uJ |
| $\mathrm{E}_{\text {ts }}$ | Total Switching Loss |  | - | 1665 | - | uJ |
| $\mathrm{t}_{\mathrm{d}(\mathrm{on})}$ | Turn-On Delay Time | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}}=600 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=25 \mathrm{~A}, \\ & \mathrm{R}_{\mathrm{G}}=10 \Omega, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V}, \\ & \text { Resistive Load,, } \mathrm{T}_{\mathrm{C}}=175^{\circ} \mathrm{C} \end{aligned}$ | - | 21.2 | - | ns |
| $\mathrm{t}_{\mathrm{r}}$ | Rise Time |  | - | 304 | - | ns |
| $\mathrm{t}_{\mathrm{d} \text { (off) }}$ | Turn-Off Delay Time |  | - | 490 | - | ns |
| $\mathrm{t}_{\mathrm{f}}$ | Fall Time |  | - | 232 | - | ns |
| $\mathrm{E}_{\text {on }}$ | Turn-On Switching Loss |  | - | 1310 | - | uJ |
| $\mathrm{E}_{\text {off }}$ | Turn-Off Switching Loss |  | - | 952 | - | uJ |
| $\mathrm{E}_{\text {ts }}$ | Total Switching Loss |  | - | 2262 | - | uJ |
| $\mathrm{Q}_{\mathrm{g}}$ | Total Gate Charge | $\begin{aligned} & \mathrm{V}_{C E}=600 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=25 \mathrm{~A}, \\ & \mathrm{~V}_{G E}=15 \mathrm{~V} \end{aligned}$ | - | 204 | - | nC |
| $\mathrm{Q}_{\text {ge }}$ | Gate to Emitter Charge |  | - | 15 | - | nC |
| $\mathrm{Q}_{\mathrm{gc}}$ | Gate to Collector Charge |  | - | 103 | - | nC |

## Typical Performance Characteristics

Figure 1. Typical Output Characteristics


Figure 3. Typical Saturation Voltage Characteristics


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level


Figure 2. Typical Output Characteristics


Figure 4. Transfer Characteristics


Figure 6. Saturation Voltage vs. $\mathbf{V}_{\text {GE }}$


## Typical Performance Characteristics

Figure 7. Saturation Voltage vs. $\mathrm{V}_{\mathrm{GE}}$


Figure 9. Gate charge Characteristics


Figure 11. Turn-on Characteristics vs. Gate Resistance


Figure 8. Capacitance Characteristics


Figure 10. SOA Characteristics


Figure 12. Turn-off Characteristics vs. Gate Resistance


## Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Collector Current


Figure 15. Switching Loss vs. Gate Resistance


Figure 17. Turn off Switching SOA Characteristics


Figure 14. Turn-off Characteristics vs. Collector Current


Figure 16. Switching Loss vs. Collector Current


Figure 18. Forward Characteristics


## Typical Performance Characteristics

Figure 19. Transient Thermal Impedance of IGBT




#### Abstract

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